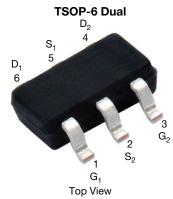
SQ3989EV

www.vishay.com

Vishay Siliconix

Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



Marking code: 9B

PRODUCT SUMMARY				
V _{DS} (V)	-30			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	-0.155			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 \text{ V}$	-0.300			
I _D (A)	-2.32			
Configuration	Dual			

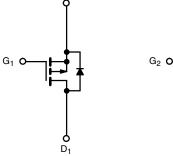
FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

S



RoHS COMPLIANT HALOGEN FREE





 S_2

P-Channel MOSFET

P-Channel MOSFET

ORDERING INFORMATION			
Package	TSOP-6		
Lead (Pb)-free and halogen-free	SQ3989EV (for detailed order number please see <u>www.vishay.com/doc?79771</u>)		

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-30		
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain surrent $(T_{1} - 150 \circ C)^{3}$	T _C = 25 °C		-2.5		
Continuous drain current (T _J = 150 °C) ^a	T _C = 125 °C	I _D	-1.5	•	
Pulsed drain current		I _{DM}	-10.2	- A	
Continuous source current (diode conduction) ^a	IS	-2.1			
Maximum neuror discipation 2	T _C = 25 °C	Pn	1.67		
Maximum power dissipation ^a	T _C = 125 °C		0.56		
Unclamped inductive surge UIS		I _{AV}	-7	А	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Maximum junction-to-ambient ^a	Steady state	R _{thJA}	150	°C/W	
Maximum junction-to-foot (drain)	Steady state	R _{thJF}	90	0/00	

Note

a. Surface mounted on 1" x 1" FR4 board

1

Vishay Siliconix

SQ3989EV

VISHAY	
	W

/ww.vishay.com

SPECIFICATIONS (T _J = 25°C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Gate threshold voltage	V _{GS(th)}	V _{DS}	_S = V _{GS} , I _D = -250 μA	-0.6	-	-1.5	V	
Gate-body leakage	I _{GSS}	V _{DS}	$_{\rm S}$ = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
Zero gate voltage drain	1	$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1	μA	
current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = -30 V, T_J = 55 °C	-	-	-5		
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-4	-	-	А	
Drain-source on-state	D	$V_{GS} = -10 V$	I _D = -0.4 A	-	0.140	0.155	Ω	
resistance a R _{DS(on)}		$V_{GS} = -4.5 V$	I _D = -0.2 A	-	0.265	0.300		
Forward transconductance ^a	9 _{fs}	V _{DS} = -5 V, I _D = -1 A		-	2.2	-	S	
Diode forward voltage ^a	V _{SD}	I _S = -0.5 A, V _{GS} = 0 V		-	-0.83	-1.1	V	
Dynamic ^b								
Total gate charge	Qg			-	8.6	11.1		
Gate-source charge	Q _{gs}	$V_{GS} = -10 V$	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -3 \text{ A}$	-	1.2	- nC	nC	
Gate-drain charge	Q _{gd}			-	3	-]	
Gate resistance	Rg	f = 1 MHz		2.5	-	7.2	Ω	
Turn-on delay time	t _{d(on)}	$V_{DD} = -10 \text{ V}, \text{ R}_{L} = 10 \Omega$ $\text{I}_{D} \cong -1 \text{ A}, \text{ V}_{GEN} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	5.7	8		
Rise time	t _r			-	3	4	- ns	
Turn-off delay time	t _{d(off)}			-	13.8	18		
Fall time	t _f			-	2	3		

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

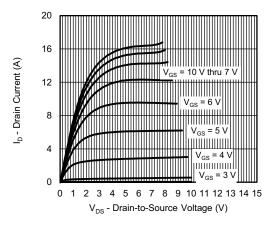
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



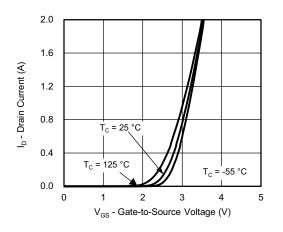
SQ3989EV

Vishay Siliconix

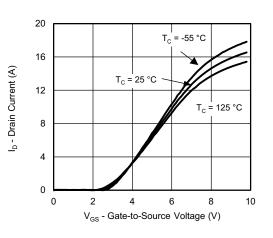
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



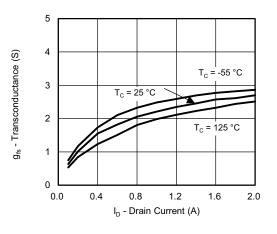
Output Characteristics



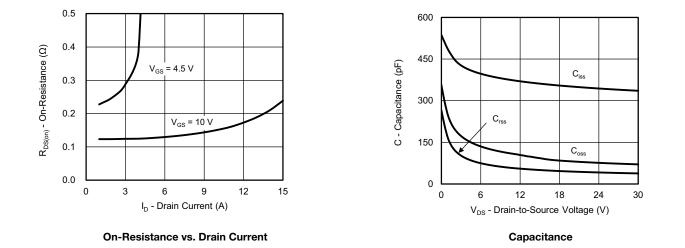
Transfer Characteristics



Transfer Characteristics



Transconductance



S22-0224-Rev. E, 07-Mar-2022

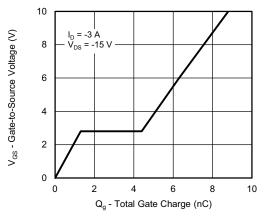
3 s. contact: automostechsi Document Number: 75059

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

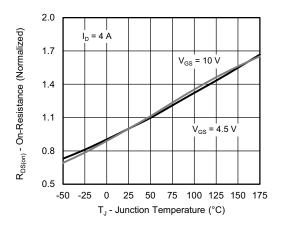


Vishay Siliconix

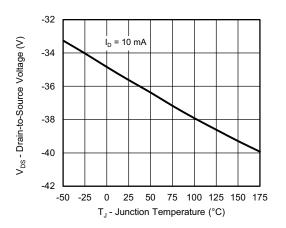
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)

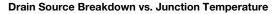


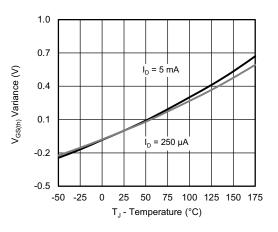
Gate Charge



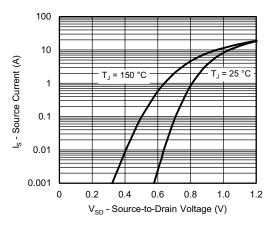
On-Resistance vs. Junction Temperature



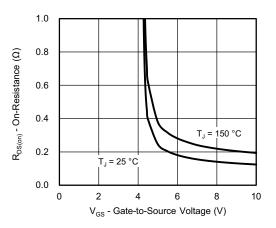




Threshold Voltage



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

4

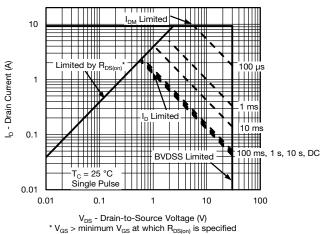
Document Number: 75059

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u> VISHAY. www.vishay.com

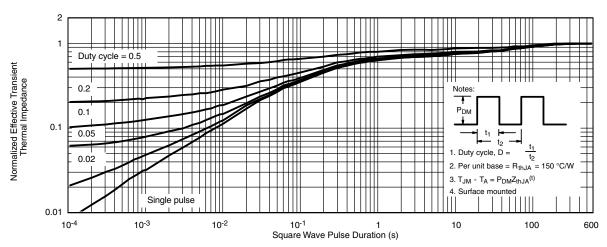
SQ3989EV

Vishay Siliconix

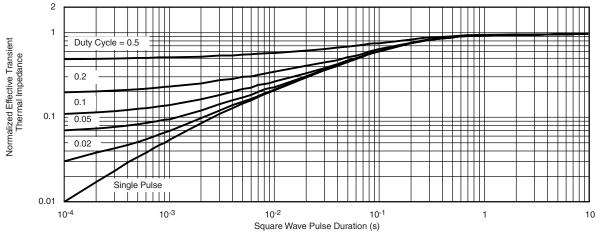
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg275059.

5

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Package Information

Vishay Siliconix

TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



	MILLIMETERS			I	NCHES	
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
Е	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е	0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁		0.60 Ref			0.024 Ref	
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom				7° Nom	
ECN: C DWG: 5		ev. I, 18-Dec	c-06			

PAD Pattern



Vishay Siliconix

Recommended Land Pattern For TSOP-5L / TSOP-6L





TSOP 5L





Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022	
DWG: 3010	

1



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.